

1 39. (New) A semiconductor laser according to Claim 1,  
2 wherein the current-blocking layer is comprised of at least one of  
3 AlInP and  $(Al_xGa_{1-x})yIn_{1-y}P$ , where  $0.7 < x < 1$  and  $y = 0.5$ .

1 40. (New) A semiconductor laser according to Claim 12,  
2 wherein the current-blocking layer is comprised of at least one of  
3 AlInP and  $(Al_xGa_{1-x})yIn_{1-y}P$ , where  $0.7 < x < 1$  and  $y = 0.5$ .

1 41. (New) A semiconductor laser according to Claim 25,  
2 wherein the current-blocking layer is comprised of at least one of  
3 AlInP and  $(Al_xGa_{1-x})yIn_{1-y}P$ , where  $0.7 < x < 1$  and  $y = 0.5$ .

1 42. (New) A semiconductor laser according to Claim 35,  
2 wherein the current-blocking layer is comprised of at least one of  
3 AlInP and  $(Al_xGa_{1-x})yIn_{1-y}P$ , where  $0.7 < x < 1$  and  $y = 0.5$ .

1 43. (New) A semiconductor laser according to Claim 36,  
2 wherein the current-blocking layer is comprised of at least one of  
3 AlInP and  $(Al_xGa_{1-x})yIn_{1-y}P$ , where  $0.7 < x < 1$  and  $y = 0.5$ .